N-Channel 80 V (D-S) MOSFET

PRODUCT SUMMARY			
V_{DS} (V)	$R_{DS(on)}$ (mΩ) MAX.	I_D (A)	Q_g (TYP.)
80	1.2 at V_{GS} = 10 V	300	253 nC

FEATURES

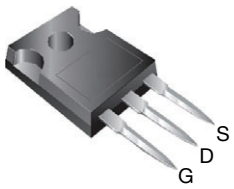
- DT-TrenchPower MOSFET
- 100 % R_g and UIS tested
- Improved dv/dt capability

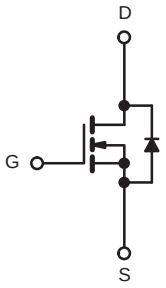
RoHS COMPLIANT

APPLICATIONS

- Power supplies:
  - Uninterruptible power supplies
  - AC/DC switch-mode power supplies
  - Lighting
- Synchronous rectification
- DC/DC converter
- Motor drive switch
- Hard Switched and High Frequency Circuits

TO-247AC





N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T_C = 25 °C, unless otherwise noted)				
PARAMETER			LIMIT	UNIT
Drain-Source Voltage		V_{DS}	80	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current (T_J = 150 °C)	T_C = 25 °C	I_D	300	A
	T_C = 100 °C		175	
Pulsed Drain Current (t = 100 µs)		I_{DM}	1250	
Avalanche Current	L = 0.1 mH	I_{AS}	100	
Single Avalanche Energy [a]		E_{AS}	3395	mJ
Maximum Power Dissipation [a]	T_C = 25 °C	P_D	442 [b]	W
	T_C = 125 °C		88.4 [b]	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to +150	°C

THERMAL RESISTANCE RATINGS			
PARAMETER		LIMIT	UNIT
Junction-to-Ambient (PCB Mount) [c]	R_{thJA}	60	°C/W
Junction-to-Case (Drain)	R_{thJC}	0.4	

Notes

a. Duty cycle ≤ 1 %.

b. See SOA curve for voltage derating.

c. When mounted on 1" square PCB (FR4 material).

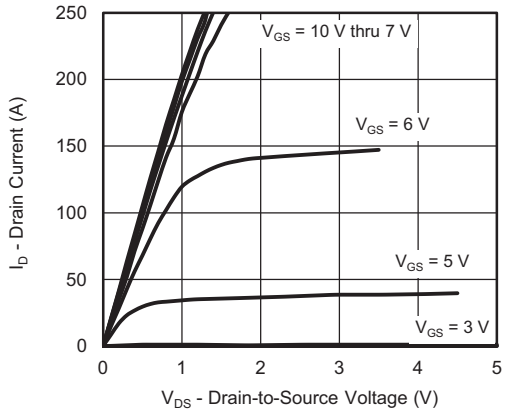
SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)						
PARAMETER	**SYMBOL**	**TEST CONDITIONS**	**MIN.**	**TYP.**	**MAX.**	**UNIT**
Static						
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = 250 µA	80	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA	1.2	-	2.5	
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V	-	-	± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 80 V, V_{GS} = 0 V	-	-	1	µA
		V_{DS} = 64 V, V_{GS} = 0 V, T_J = 85 °C	-	-	10	
Drain-Source On-State Resistance [a]	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 20 A	-	1.2	1.6	mΩ
Forward Transconductance [a]	g_{fs}	V_{DS} = 15 V, I_D = 3 A	-	22	-	S
Dynamic [b]						
Input Capacitance	C_{iss}	V_{GS} = 0 V, V_{DS} = 40 V, f = 1 MHz	-	15630	-	pF
Output Capacitance	C_{oss}		-	3295	-	
Reverse Transfer Capacitance	C_{rss}		-	290	-	
Total Gate Charge [c]	Q_g	V_{DS} = 40 V, V_{GS} = 10 V, I_D = 30 A	-	253	-	nC
Gate-Source Charge [c]	Q_{gs}		-	39	-	
Gate-Drain Charge [c]	Q_{gd}		-	82	-	
Gate Resistance	R_g	f = 1 MHz	-	1.0	-	Ω
Turn-On Delay Time [c]	$t_{d(on)}$	V_{DD} = 40 V, R_L = 1.67 Ω I_D ≅ 30 A, V_{GEN} = 10 V, R_g = 1 Ω	-	53	-	ns
Rise Time [c]	t_r		-	220	-	
Turn-Off Delay Time [c]	$t_{d(off)}$		-	167	-	
Fall Time [c]	t_f		-	180	-	
Drain-Source Body Diode Ratings and Characteristics [b] (T_C = 25 °C)						
Pulsed Current (t = 100 µs)	I_{SM}		-	-	1250	A
Forward Voltage [a]	V_{SD}	I_F = 30 A, V_{GS} = 0 V	-	-	1.0	V
Reverse Recovery Time	t_{rr}	I_F = 30 A, di/dt = 100 A/µs	-	120	-	ns
Peak Reverse Recovery Charge	$I_{RM(REC)}$		-	7	-	A
Reverse Recovery Charge	Q_{rr}		-	350	-	nC

Notes

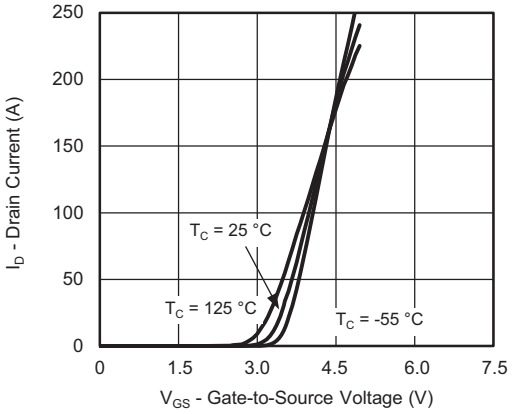
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.
c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

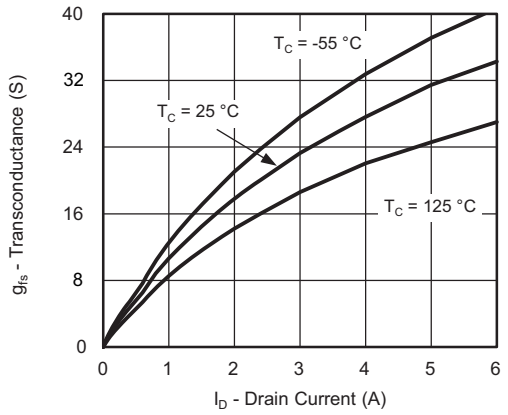
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



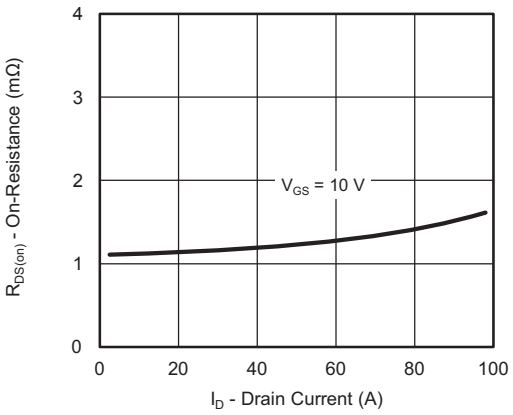
Output Characteristics



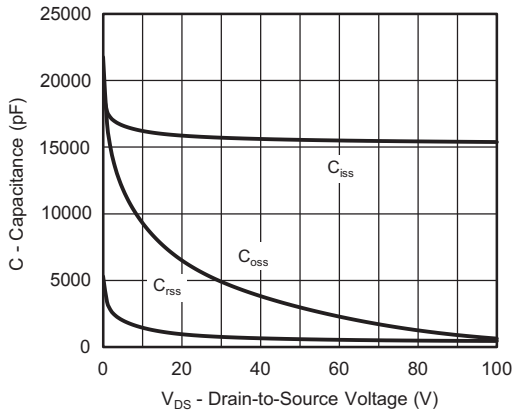
Transfer Characteristics



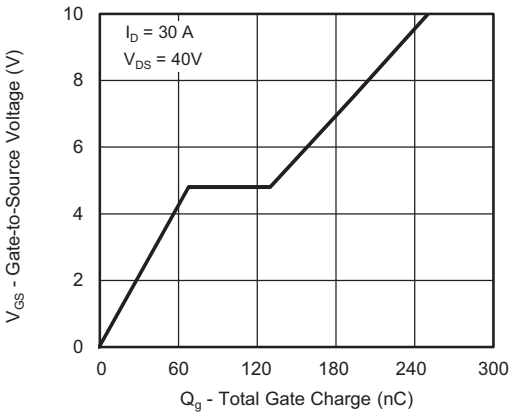
Transconductance



On-Resistance vs. Drain Current

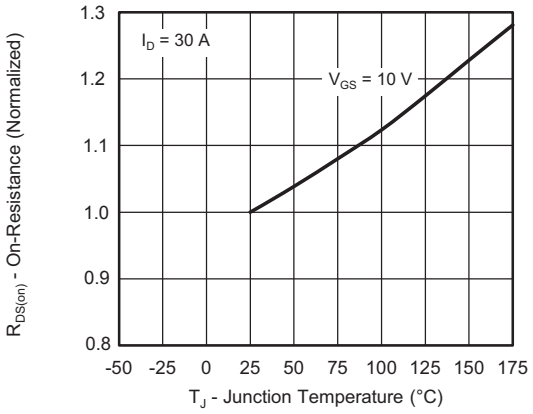


Capacitance

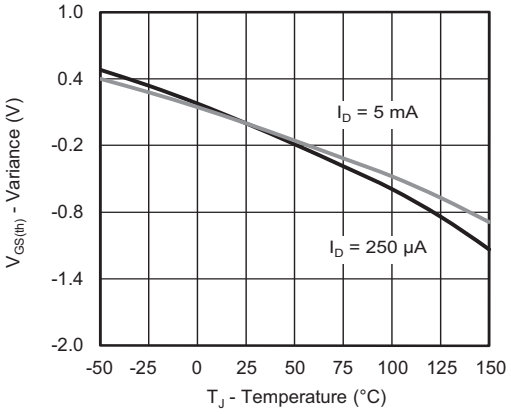


Gate Charge

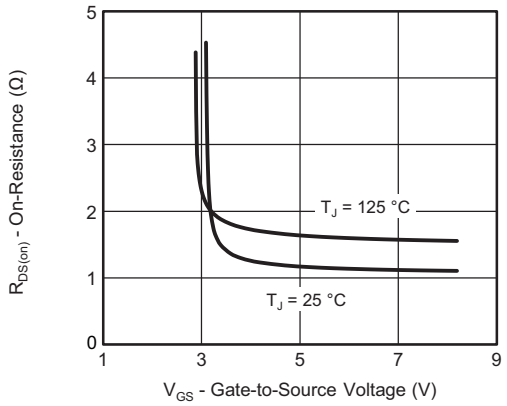
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



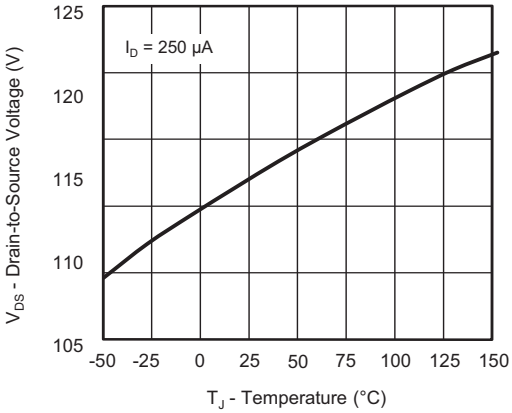
On-Resistance vs. Junction Temperature



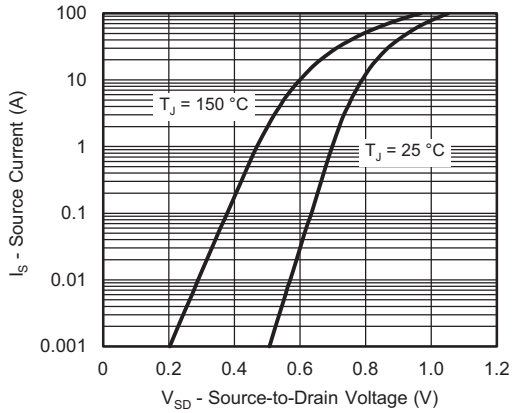
Threshold Voltage



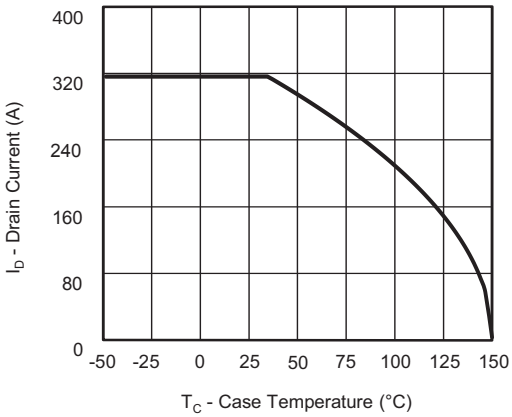
On-Resistance vs. Gate-to-Source Voltage



Drain Source Breakdown vs. Junction Temperature

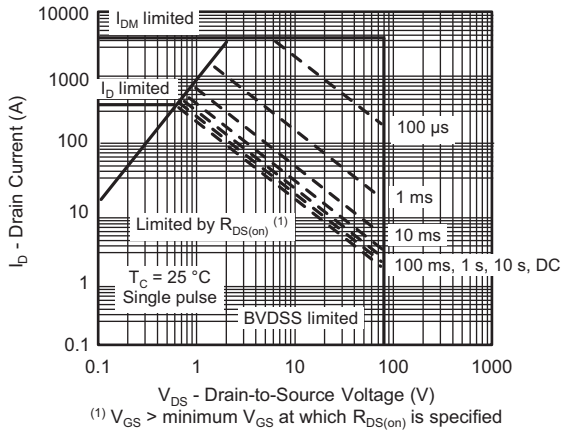


Source Drain Diode Forward Voltage

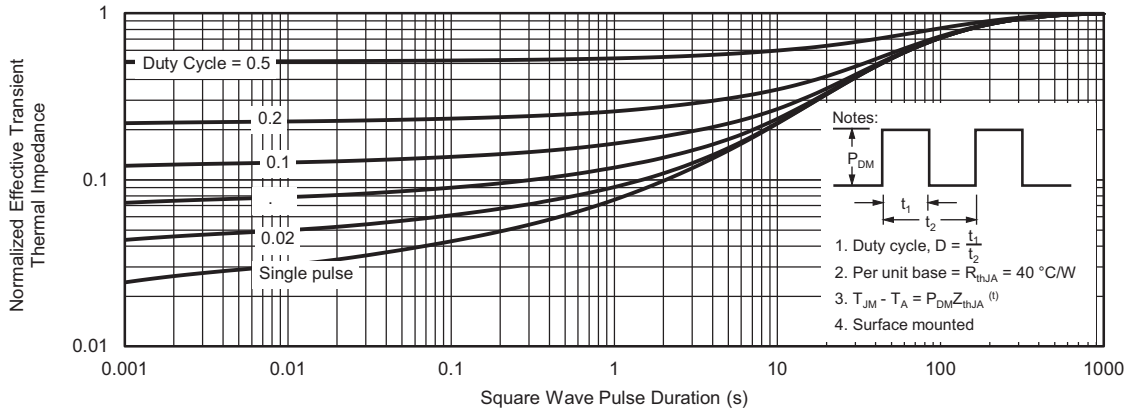


Current De-Rating

THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)

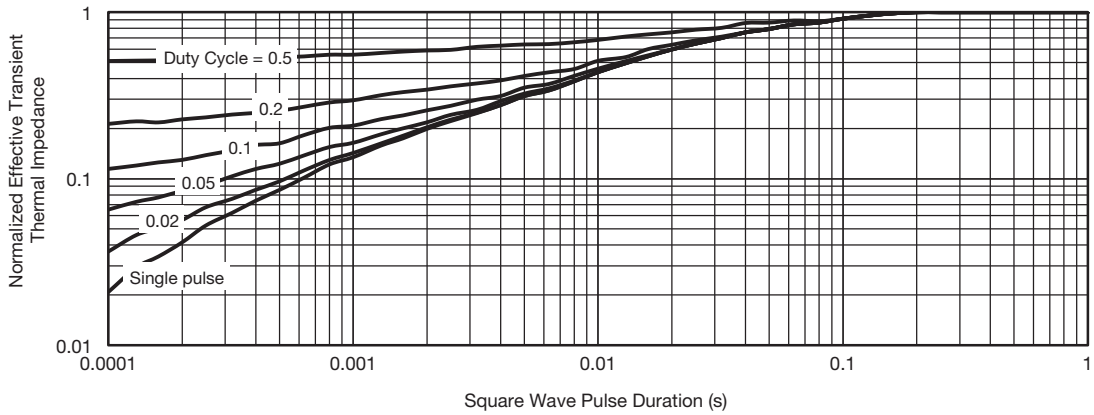


Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient

THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



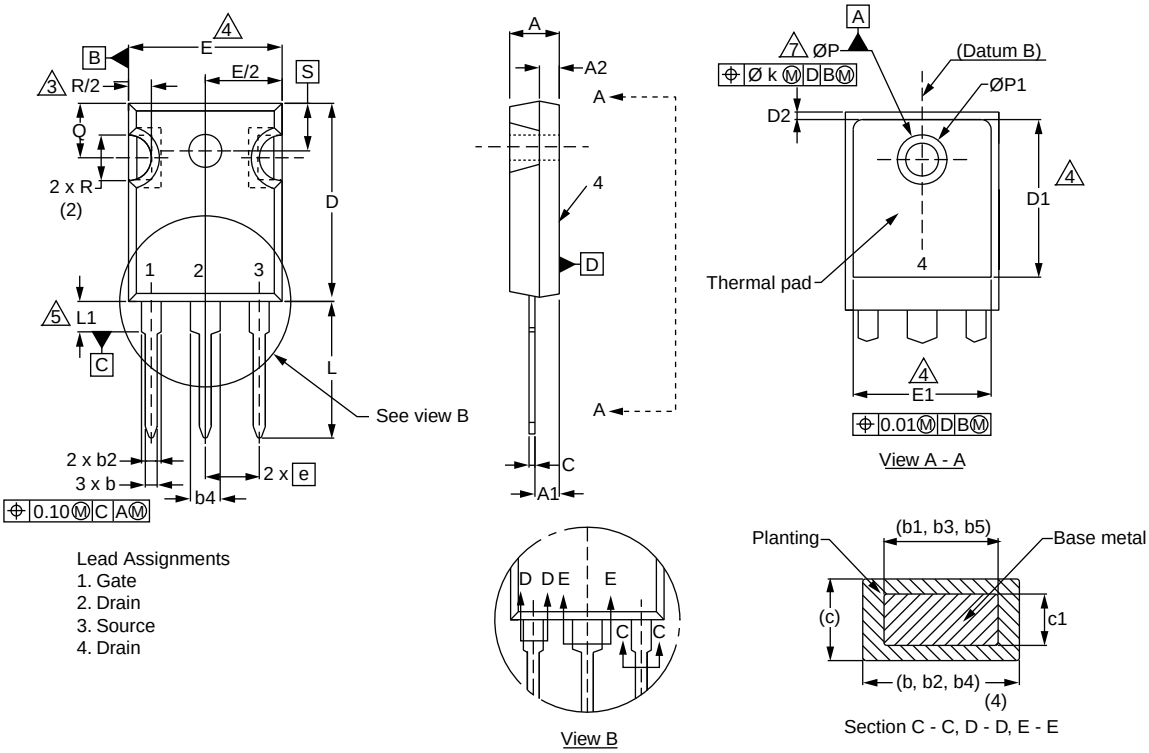
Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction to Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction to Case (25 °C)

  are given for general guidelines only to enable the user to get a “ball park” indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

TO-247AC (High Voltage)



Lead Assignments
1. Gate
2. Drain
3. Source
4. Drain

	MILLIMETERS		INCHES	
DIM.	MIN.	MAX.	MIN.	MAX.
A	4.58	5.31	0.180	0.209
A1	2.21	2.59	0.087	0.102
A2	1.17	2.49	0.046	0.098
b	0.99	1.40	0.039	0.055
b1	0.99	1.35	0.039	0.053
b2	1.53	2.39	0.060	0.094
b3	1.65	2.37	0.065	0.093
b4	2.42	3.43	0.095	0.135
b5	2.59	3.38	0.102	0.133
c	0.38	0.86	0.015	0.034
c1	0.38	0.76	0.015	0.030
D	19.71	20.82	0.776	0.820
D1	13.08	-	0.515	-

	MILLIMETERS		INCHES	
DIM.	MIN.	MAX.	MIN.	MAX.
D2	0.51	1.30	0.020	0.051
E	15.29	15.87	0.602	0.625
E1	13.72	-	0.540	-
e	5.46 BSC		0.215 BSC	
Ø k	0.254		0.010	
L	14.20	16.25	0.559	0.640
L1	3.71	4.29	0.146	0.169
N	7.62 BSC		0.300 BSC	
Ø P	3.51	3.66	0.138	0.144
Ø P1	-	7.39	-	0.291
Q	5.31	5.69	0.209	0.224
R	4.52	5.49	0.178	0.216
S	5.51 BSC		0.217 BSC	

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